

ABSTRACT OF THE DISCLOSURE

Sub C.7

A semiconductor light emitting device of double hetero junction includes an active layer and clad layers. The clad layers include an n-type layer and p-type layer. The clad layers sandwich the active layer. A band gap energy of the clad layers is larger than that of the active layer. The band gap energy of the n-type clad layer is smaller than of the p-type clad layer.

00/2200 26040950

Abstract of the Disclosure

A semiconductor light emitting device of double hetero junction comprising an active layer; and clad layers comprising an n-type layer and p-type layer, the clad layers sandwiching the active layer, a band gap energy of the clad layers being larger than that of the active layer; wherein band gap energy of the n-type clad layer is smaller than of the p-type clad layer.

09604097 062700